NEC
ELECTRON DEVICE

MOS INTEGRATED CIRCUIT
μPD3593

2 048-BIT CCD LINEAR IMAGE SENSOR WITH PERIPHERAL CIRCUITS

The μPD3593 is a 2048-bit high sensitivity CCD (Charge Coupled Device) linear image sensor which changes optical images to electrical signal.

The μPD3593 has an output amplifier which has wide output range, and which can switch gain. Therefore easy to get signal level which is easy to process from low illumination to high illumination, and it is easy to apply to many purposes.

With internal generation circuit of driving signal and internal driver, the μPD3593 performs only with two basic clock inputs. No special driving circuit is required. In addition, analog signal processor convert and output independent CCD register in every bit to continuous video signal. So it is easy to interface to A/D converter or Bi-level converter.

FEATURES

• Valid photocell	2 048-bit
• Photocell's pitch	14 μm
• CCD output	4 steps selectable gain (2, 4, 8, 16 times)
• Peak response wavelength	550 nm (green)
• Resolution	8 dot/mm across the shorter side of a B4-size (257 x 364 mm) sheet
• Power supply	+12 V, +5 V
• Drive clock level	CMOS 5 V clock input x 2
• High speed scan	1 ms/line
• Built-in circuit	Timing generator
	CCD clock driver
	Optical black clamp circuit
	Sample and hold circuit
	4-step valiable gain amplifier

ORDERING INFORMATION

Part Number	Package	Quality Grade
μPD3593D	22-pin ceramic DIP (CERDIP) (400 mil)	Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

The information contained in this document is being issued in advanced of the production cycle for the device. The parameters for the device may change before final production or NEC Corporation, at its own discretion, may withdraw the device prior to its production.

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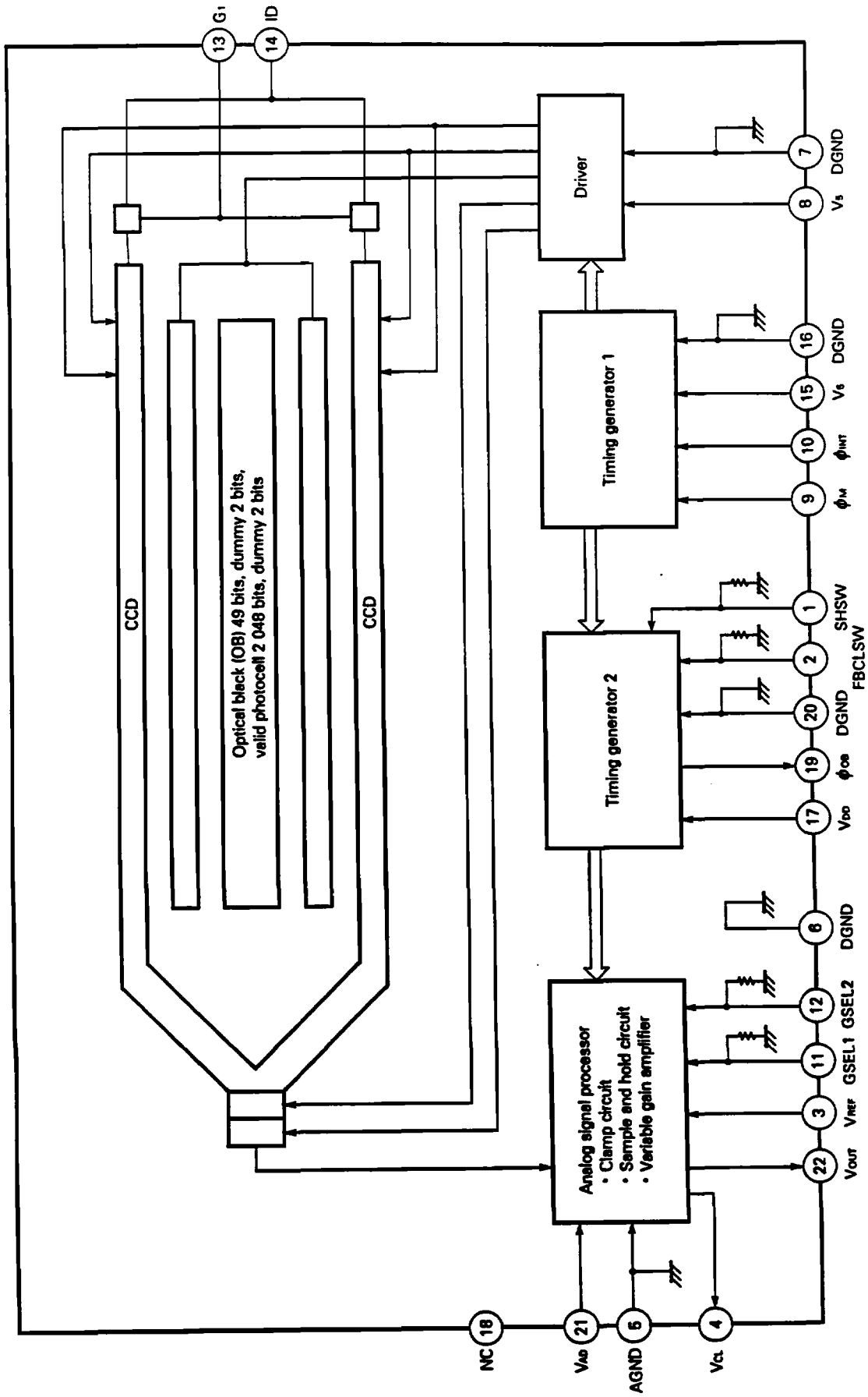
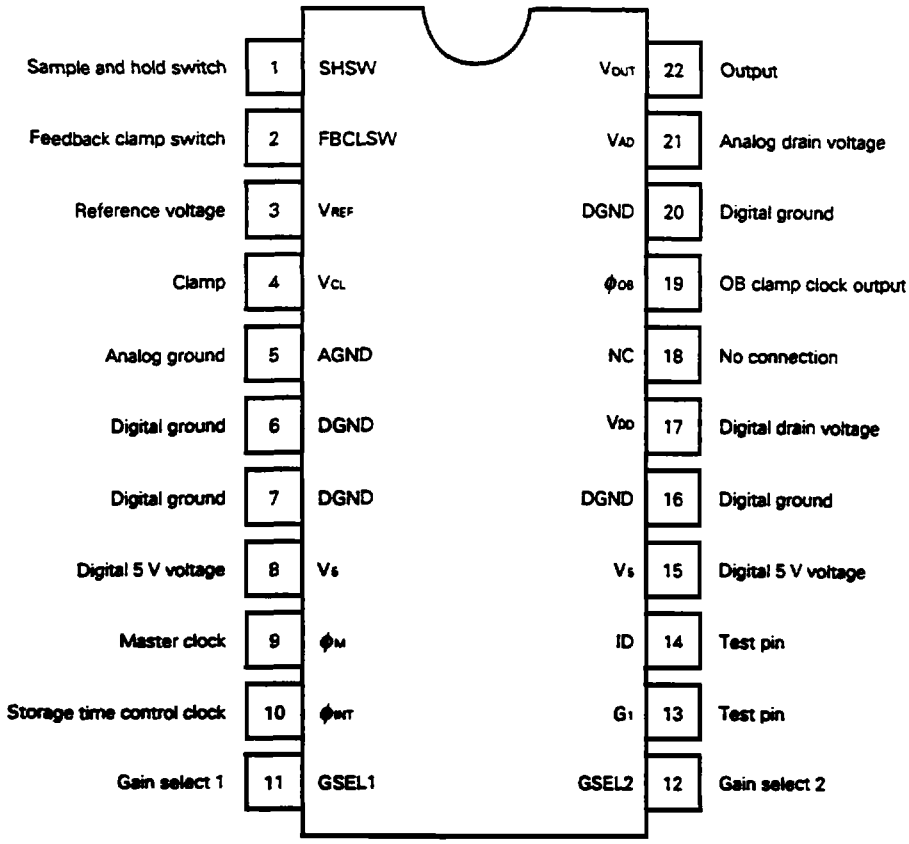
BLOCK DIAGRAM



PIN CONFIGURATION (Top View)



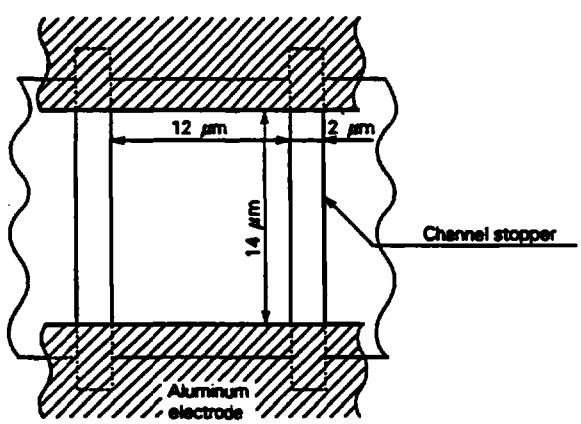
Function of SHSW pin

SHSW	Sample and hold circuit
VS	Stop
0 V	Operate

Function of FBCLSW pin

FBCLSW	Feedback clamp circuit
VS	Stop
0 V	Operate

PHOTOELEMENT STRUCTURE DIAGRAM



ABSOLUTE MAXIMUM RATINGS (T_a = 25 ° C)

Parameter	Symbol	Ratings	Unit
Analog drain voltage	V_{AD}	−0.3 ~ +15	V
Digital drain voltage	V_{DD}	−0.3 ~ +15	V
Test pin ID voltage	V_{ID}	−0.3 ~ +15	V
Digital 5 V voltage	V_S	−0.3 ~ +7	V
Reference voltage	V_{REF}	−0.3 ~ +7	V
Clamp pin input voltage	V_{CL}	−0.3 ~ +7	V
Sample and hold switch	V_{SHSW}	V_S	V
Feedback clamp switch	V_{FBCLSW}	V_S	V
Master clock voltage	$V_{\phi M}$	V_S	V
Storage time control clock voltage	$V_{\phi INT}$	V_S	V
Gain select input voltage 1	V_{GSEL1}	V_S	V
Gain select input voltage 2	V_{GSEL2}	V_S	V
Operating ambient temperature	T_{OPT}	−25 ~ +60	° C
Storage temperature	T_{STG}	−40 ~ +100	° C

RECOMMENDED OPERATING CONDITIONS (T_a = −25 to + 60 ° C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Analog drain voltage	V_{AD}	11.4	12.0	12.6	V
Digital drain voltage	V_{DD}	11.4	12.0	12.6	V
Test pin ID voltage	V_{ID}	11.4	12.0	12.6	V
Digital 5 V voltage	V_S	4.5	5.0	5.5	V
Reference voltage	V_{REF}	4.0	4.5	5.0	V
Master clock ϕ_M signal high level	$V_{\phi MH}$	4.5	V_S	V_S	V
Master clock ϕ_M signal low level	$V_{\phi ML}$	−0.3	0	0.5	V
Storage time control clock ϕ_{INT} signal high level	$V_{\phi INTH}$	4.5	V_S	V_S	V
Storage time control clock ϕ_{INT} signal low level	$V_{\phi INTL}$	−0.3	0	0.5	V
Gain select input voltage GSEL 1,2 signal high level	$V_{\phi GSELH}$	4.5	V_S	V_S	V
Gain select input voltage GSEL 1,2 signal low level (Note 1)	$V_{\phi GSELL}$	−0.3	0	0.5	V
Sample and hold switch SHSW signal high level	$V_{\phi SHH}$	4.5	V_S	V_S	V
Sample and hold switch SHSW signal low level (Note 1)	$V_{\phi SHL}$	−0.3	0	0.5	V
Feedback clamp switch FBCLSW signal high level	$V_{\phi FBCLH}$	4.5	V_S	V_S	V
Feedback clamp switch FBCLSW signal low level (Note 1)	$V_{\phi FBCLL}$	−0.3	0	0.5	V
Hold capacitor (Note 2)	C_{CL}	—	0.001	0.01	μF
Master clock ϕ_M frequency	$f_{\phi M}$	0.5	2	4	MHz

Note 1. Gain select pin (GSEL 1, 2), sample and hold switch pin (SHSW), feedback clamp switch pin (FBCLSW) are pull down to GND internally with 50 kΩ ~ 200 kΩ resistor.

2. Control voltage hold capacitor depending on storage time (T_{INT}).

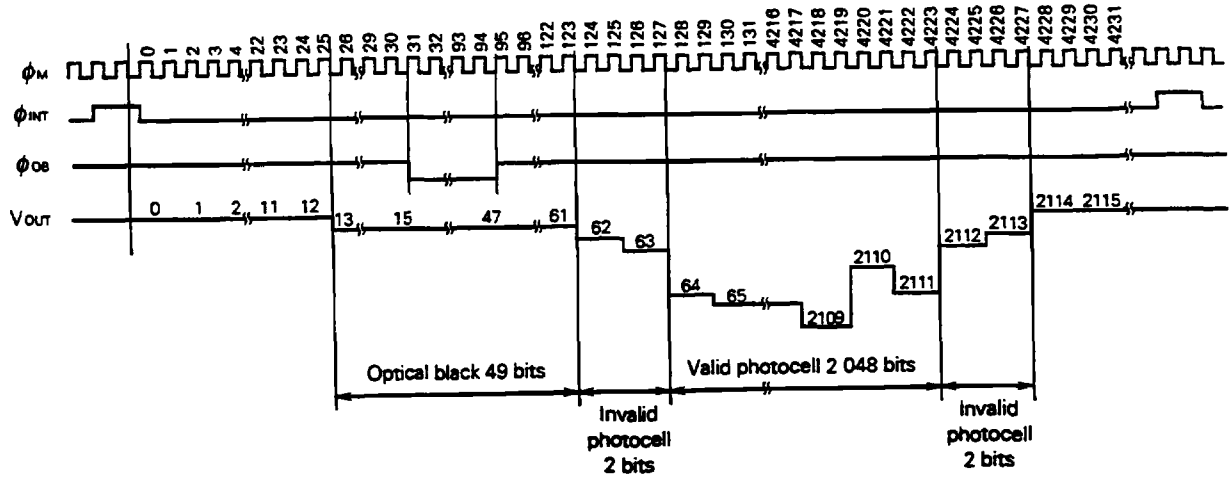
ELECTRICAL CHARACTERISTICS

T_a = 25 ° C, V_{AD} = V_{DD} = 12 V, V_S = 5 V, $f_{\phi M}$ = 2 MHz, data rate = 1 MHz, storage time = 10ms
input signal clock = 5 V_{P-P}, V_{REF} = 4.5 V, light source = 3200 K halogen lamp + C500 (infrared cut filter)

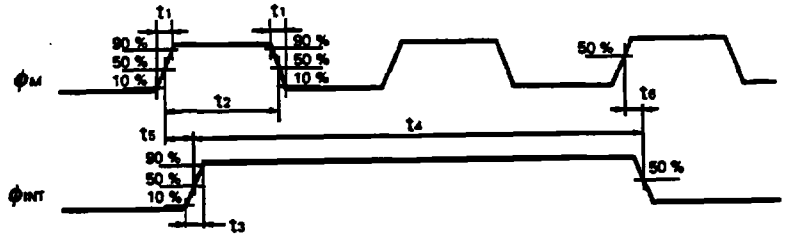
Parameter	Symbol	Test Conditions	GSEL1	GSEL2	MIN.	TYP.	MAX.	Unit	Built-in amplifier gain
Saturation voltage	V_{SAT}	Daylight color fluorescent lamp	—	—	2	3	—	V	
Saturation exposure	SE	Daylight color fluorescent lamp	0	0	—	0.114	—	lx·s	x2
			0	1	—	0.051	—		x4
			1	0	—	0.027	—		x8
			1	1	—	0.012	—		x16
Photo response non-uniformity	PRNU	V_{OUT} = 500 mV	0	0	—	±4	±8	%	
Average dark signal	ADS	T_C = 25 ° C Note, T_{INT} = 10 ms light shielding	0	0	—	1	5	mV	x2
			0	1	—	2	10		x4
			1	0	—	4	20		x8
			1	1	—	8	40		x16
Dark signal non-uniformity	DSNU	T_C = 25 ° C Note, T_{INT} = 10 ms light shielding	0	0	–5	±1	+5	mV	x2
			0	1	–10	±2	+10		x4
			1	0	–20	±4	+20		x8
			1	1	–40	±8	+40		x16
Power consumption	P_W	V_{DD} = V_{DD} = 12 V V_S = 5 V, $f_{\phi M}$ = 2 MHz	0	0	150	230	350	mW	
			1	1	80	120	180		
Output impedance	Z_O		0	0	-	1	2	kΩ	
Response	R_F	Daylight color fluorescent lamp	0	0	18.5	26.4	34.3	V/lx·s	x2
			0	1	—	59.4	—		x4
			1	0	—	110	—		x8
			1	1	—	248	—		x16
Response peak wavelength			—	—	—	550	—	nm	
Image lag	IL	V_{OUT} = 1 V	0	0	—	2	5	%	
Reference voltage input current	I_{REF}		0	0	—	0.001	0.1	mA	
Transfer efficiency	TTE	V_{OUT} = 500 mV	0	0	92	98	—	%	
Sample and hold noise	SHN	light shielding	0	0	—	15	30	mV	
Clamp error	V_{BIAS}	light shielding V_{REF} = 4.5 V	0	0	–100	0	+100	mV	
Clock input capacitance Master clock input pin Storage time control clock input pin	$C_{\phi 1}$		—	—	—	5	10	pF	
Pull down resistor Gain select input pin Sample and hold switch pin Feedback clamp switch pin	R_{PD}	V_{IN} = 5 V	—	—	50	100	200	kΩ	
Resister imbalance	RI	V_{OUT} = 500 mV	0	0	—	—	3	%	
Dynamic range	DR	V_{SAT}/DSNU	0	0	—	3000	—	times	x2
			0	1	—	1500	—		x4
			1	0	—	750	—		x8
			1	1	—	375	—		x16

Note Tc = Case temperature

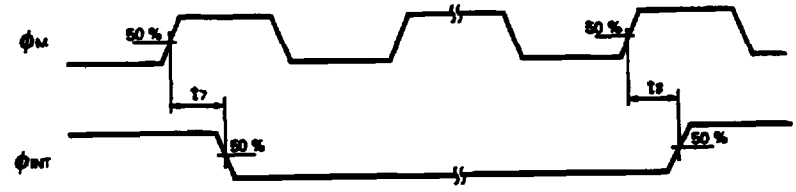
TIMING CHART



Timing Chart for ϕ_M and ϕ_{INT}



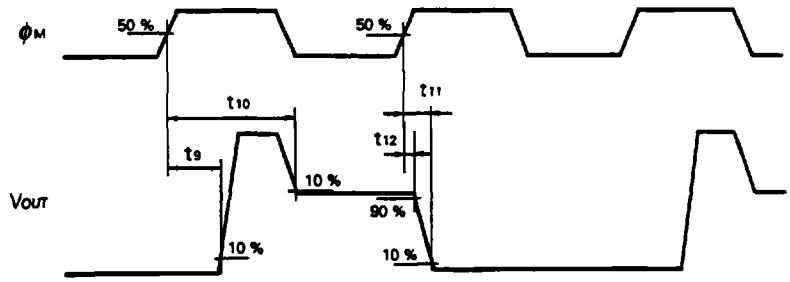
ϕ_{OB} Signal Delay from ϕ_M



Recommended Timing (Unit: ns)

Parameter	MIN.	TYP.	MAX.
t_1	0	20	100
t_2	125	250	1000
t_3	0	20	100
t_4	—	4t_2	—
t_5	-30	0	t_2
t_6	-t_2	0	t_2

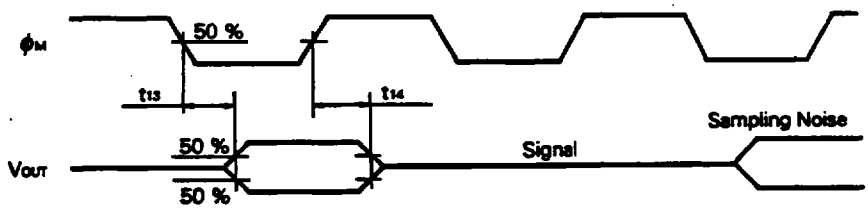
VOUT Signal Delay from ϕ_M (SHSW pin = VS)



Signal Delay Time at VOUT = 500 mV (Unit: ns)

Parameter	MIN.	TYP.	MAX.
t_7	200	280	370
t_8	150	220	290
t_9	40	60	80
t_{10}	160	230	300
t_{11}	66	95	125
t_{12}	40	60	80

VOUT Signal Delay from ϕ_M (SHSW pin = 0 V)



Signal Delay Time (Unit: ns)

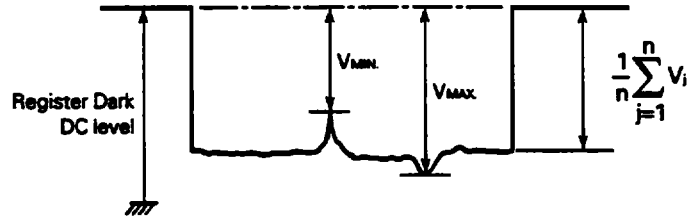
Parameter	MIN.	TYP.	MAX.
t_{13}		80	120
t_{14}		50	100

DEFINITIONS OF CHARACTERISTIC ITEMS

1. Saturation voltage: V_{SAT}
   Output signal voltage at which the response linearity is lost.
2. Saturation exposure: SE
   Product of intensity of illumination (lx) and storage time (s) when saturation of output voltage occurs.
3. Photo response non-uniformity: PRNU
   The peak/bottom ratio to the average output voltage of all the valid bits calculated by the following formula.

$$PRNU\ (\%) = \left(\frac{V_{MAX.}\ \text{or}\ V_{MIN.}}{\frac{1}{n}\sum_{j=1}^{n} V_j} - 1 \right) \times 100$$

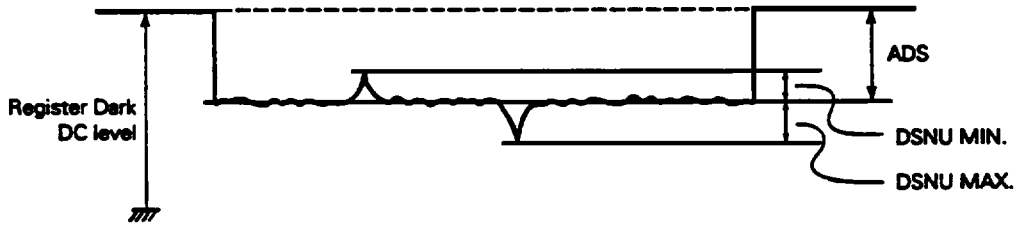
n : Number of valid bits
V_j : Output voltage of each bit



4. Average dark signal: ADS
   Output average voltage in light shielding

$$ADS(mV) = \frac{1}{n}\sum_{j=1}^{n} V_j$$

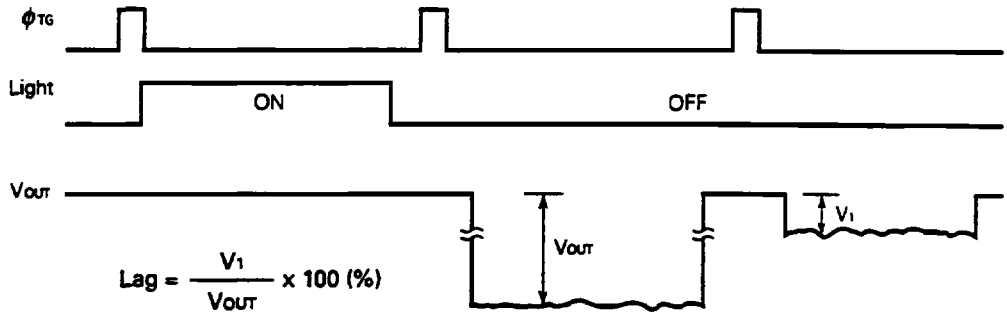
5. Dark signal non-uniformity: DSNU
   The difference between peak or bottom output voltage in light shielding and ADS.



6. Output impedance: Z_o
   Output pin impedance viewed from outside.
7. Response: R
   Output voltage divided by exposure (lx·s).
   Note that the response varies with the light source.

8. Image Lag: IL

The rate between the last output voltage and the next one after read out the data of a line.



$$\text{Lag} = \frac{V_1}{V_{OUT}} \times 100\ (\%)$$

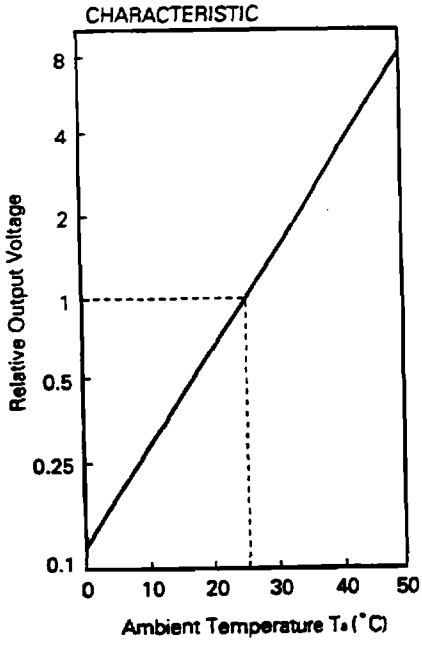
9. Resister Imbalance: RI

The rate of the average voltage which is the difference between the output voltage of Odd and Even bits, against the average output voltage of all the valid bits.

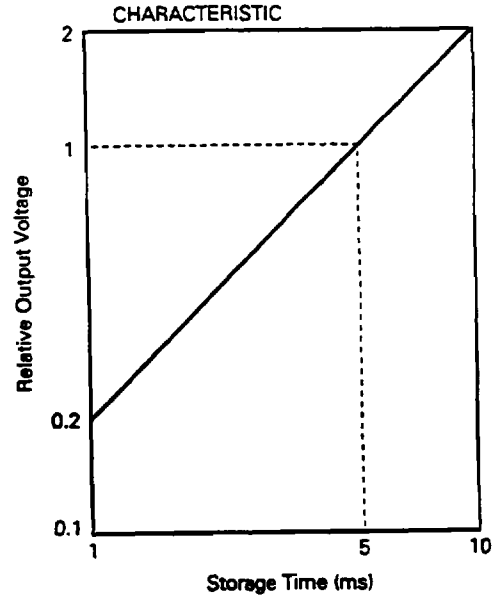
$$RI = \frac{\frac{1}{n}\sum_{j=1}^{n} |V_j - V_{j+1}|}{\frac{1}{n}\sum_{j=1}^{n} V_j} \times 100\ (\%)$$

STANDARD CHARACTERISTIC CURVES (T_a = 25 ° C)

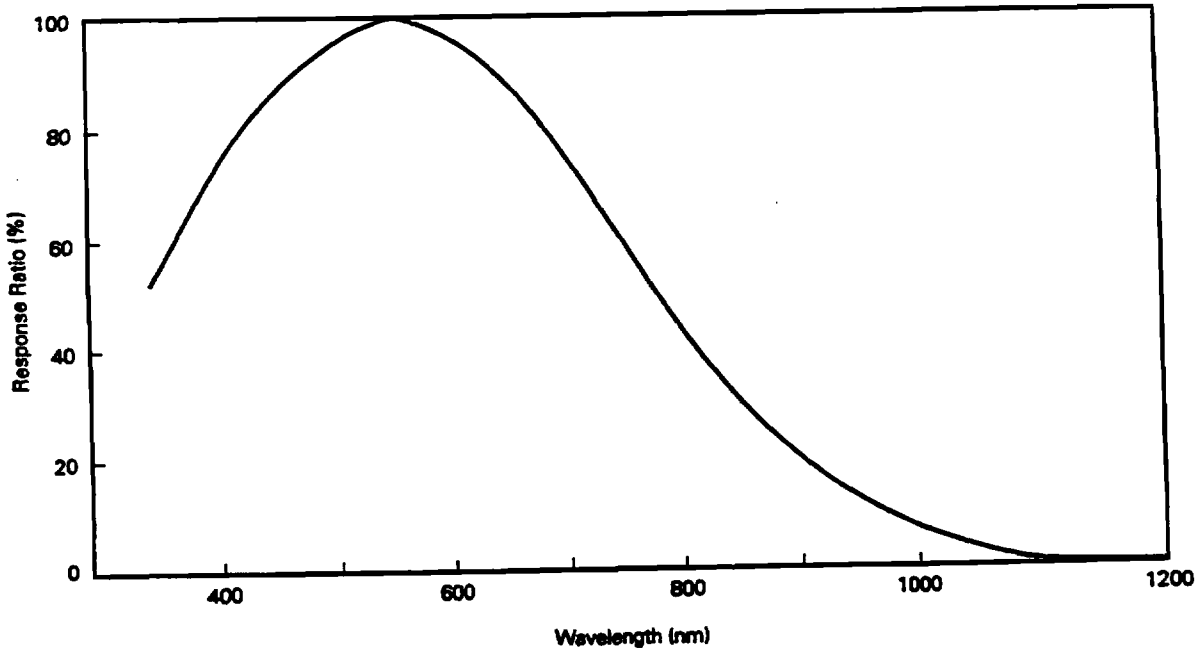
DARK OUTPUT TEMPERATURE CHARACTERISTIC



STORAGE TIME OUTPUT VOLTAGE CHARACTERISTIC

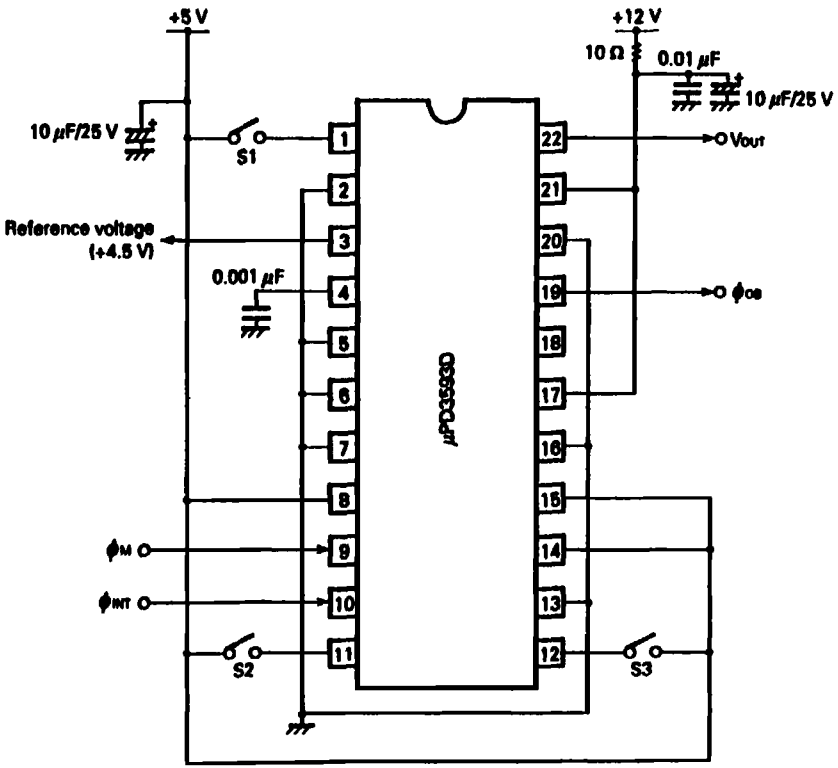


SPECTRAL RESPONSE CHARACTERISTIC



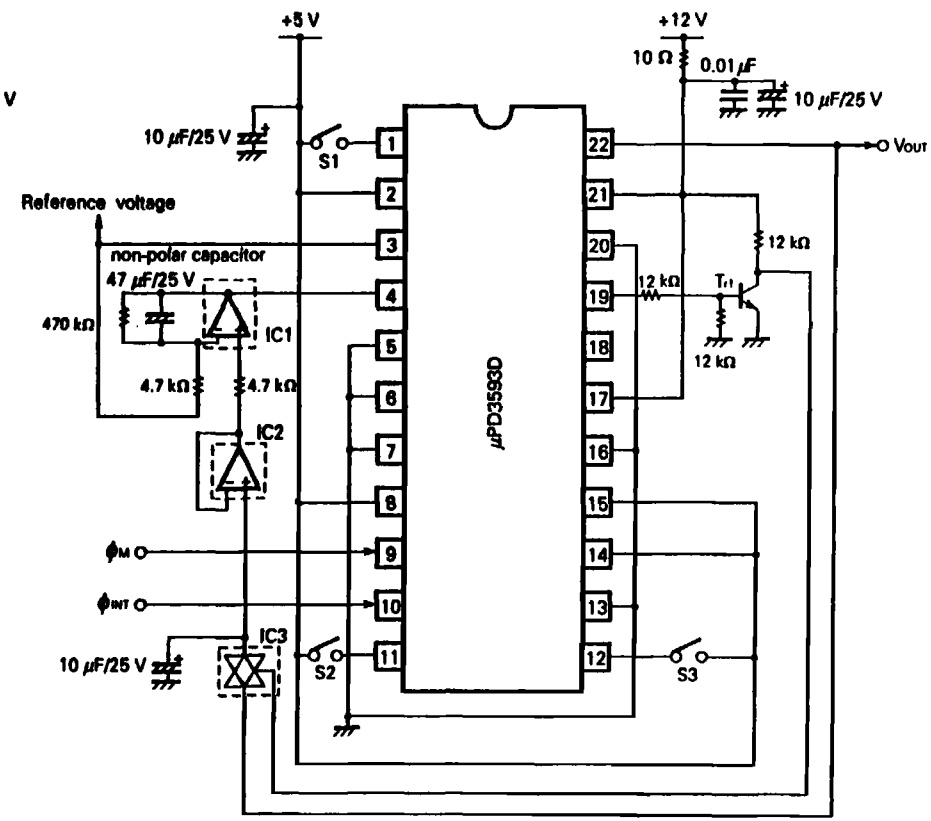
APPLICATION EXAMPLES

Example 1: With internal feedback clamp



S1: Sample and hold use/unuse select switch
(OFF; Use ON; Unuse)
S2, S3: Output amplifier gain select switch

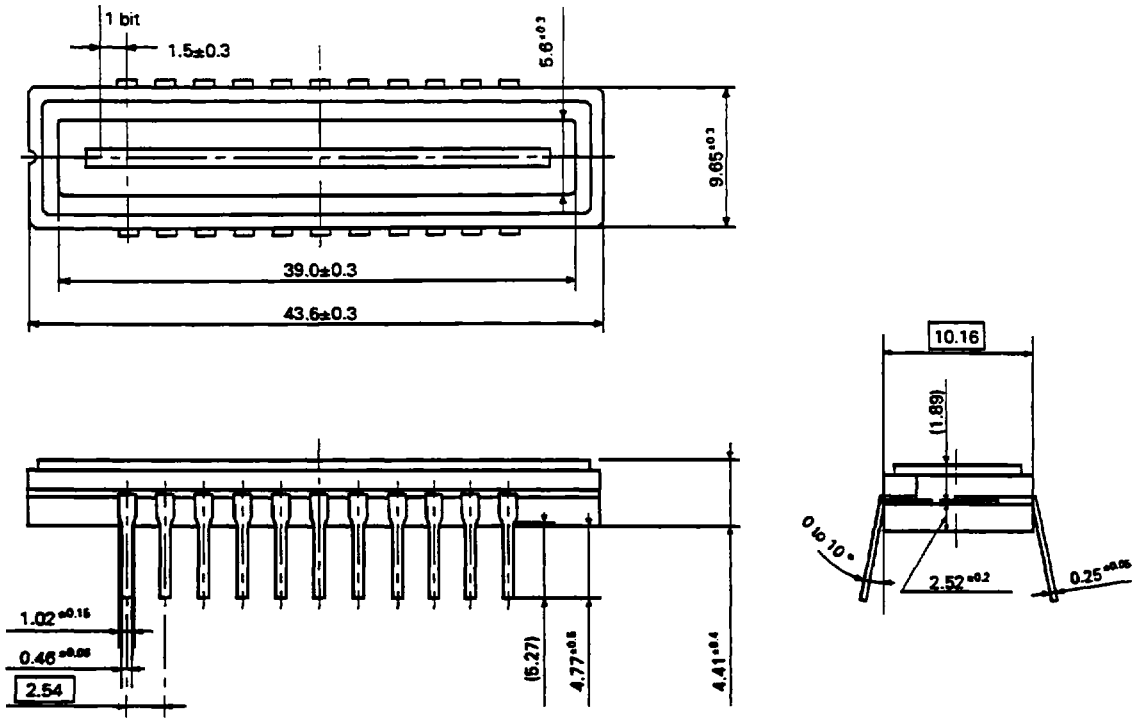
Example 2: Without internal feedback clamp



IC1, IC2: Low offset, low input current
IC3: μPD4066
Tr1: 2SC945

The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

PACKAGE DIMENSIONS (Unit: mm)



Name	Dimensions	Refractive index
Glass cap	42.2 x 9.0 x 0.5	1.5